

A better understanding of the gas gain in GEM detectors

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GEM DETECTOS:

For <u>Gas Electron Multiplier</u> (GEM) detectors a quantitative understanding of the gas gain is still lacking.



Gas gain = the multiplication factor between initial and final amount of electrons.





Effective gas gain = the multiplication factor between initial and final amount of electrons which reach the anode.



AVENUES OF EXPLORATION:

We have explored this discrepancy between experiment and theory in the following ways:

- Surface potential calculations
- Electron transport algorithm
- Secondary electron emission
- Asymmetries in GEM hole geometry





SURFACE POTENTIAL CALCULATIONS:

Besides the accumulation of avalanche charge on the GEM we calculate the surface potential using the surface resistivity of polyimide.

Units: $\Omega/_{\Box}$





SURFACE POTENTIAL CALCULATIONS:

Modeling the hole as a double cone and dividing it into strips:





SURFACE POTENTIAL CALCULATIONS:

Taking the width of the strips \rightarrow 0 we get an analytic solution:





ELECTRON TRANSPORT ALGORITHM:

For each free time electrons are traced on a vacuum trajectory, according to the local \vec{E} -field of the initial position of the particle:

 $\vec{E}(\vec{r},t) = \vec{E}(\vec{r}_0) = \text{Constant}$

This local field approximation in addition to the <u>null-collision technique</u> determines collision rate.



ELECTRON TRANSPORT ALGORITHM:

The Runge-Kutta-Nyström method was used to improve the accuracy of the transport algorithm.

This will allow to accurately simulate low pressure gas gain detectors (P << 1 atm).



Effective gain for a single GEM detector



SECUNDARY ELECTRON EMISSION:

In the simulations the effect of secondary electron emissions from the polyimide surface has been ignored.

The minimum energy required to release charges from impact is \sim 29 eV.

→ Neglectable effect!

Energy distribution of impact electrons





Asymmetries in the geometry of a GEM can occur due to the etching processes.









Two main production techniques are used.

- Double mask
- Single mask •

The gas gain is dependent on the orientation of the GEM.





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Different types of hole geometries have been studied:

















During the project the following possibilities have been explored:

- Surface potential calculations
- Electron transport algorithm
- Secondary electron emission
- Asymmetries in GEM hole geometry

\rightarrow No solution to the discrepancy has been found!





Feel free to ask questions!

[1] M. Alfonsi et al., CERN-LHCC-2008-011.

[2] G. Croci, Doctoral Thesis, University of Siena (2010)

[3] J. Merlin, Doctoral Thesis, University of Strasbourg (2016).



